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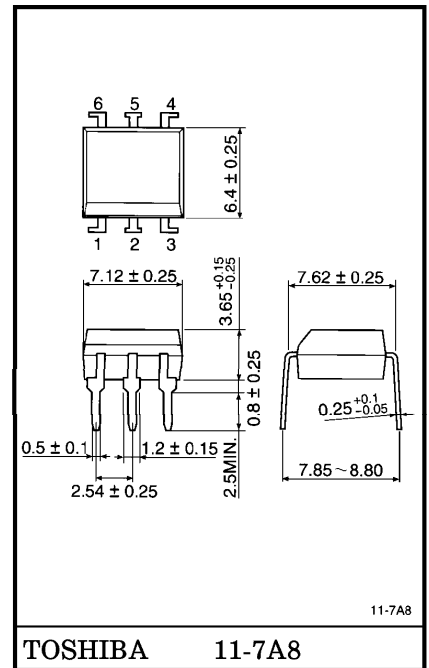
## 4N25(Short), 4N25A(Short), 4N26(Short), 4N27(Short), 4N28(Short)

- AC LINE /DIGITAL LOGIC ISOLATOR.
- DIGITAL LOGIC /DIGITAL LOGIC ISOLATOR.
- TELEPHONE LINE RECEIVER.
- TWISTED PAIR LINE RECEIVER.
- HIGH FREQUENCY POWER SUPPLY FEEDBACK CONTROL.
- RELAY CONTACT MONITOR.

The TOSHIBA 4N25 (Short) through 4N28 (Short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in-line package.

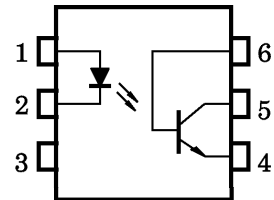
- Switching Speeds :  $3\mu\text{s}$  (Typ.)
- DC Current Transfer Ratio : 100% (Typ.)
- Isolation Resistance :  $10^{11}\Omega$  (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



Weight : 0.4g

### PIN CONFIGURATIONS (Top view)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : EMITTER
- 5 : COLLECTOR
- 6 : BASE

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Continuous)	I <sub>F</sub>	80	mA
	Forward Current Derating	ΔI <sub>F</sub> /°C	1.07 (*)	mA/°C
	Peak Forward Current (Note 1)	I <sub>PF</sub>	3	A
	Power Dissipation	P <sub>D</sub>	150	mW
	Power Dissipation Derating	ΔP <sub>D</sub> /°C	2.0 (*)	mW/°C
	Reverse Voltage	V <sub>R</sub>	3	V
DETECTOR	Collector-Emitter Voltage	BV <sub>CEO</sub>	30	V
	Collector-Base Voltage	BV <sub>CBO</sub>	70	V
	Emitter-Collector Voltage	BV <sub>ECO</sub>	7	V
	Collector Current (Continuous)	I <sub>C</sub>	100	mA
	Power Dissipation	P <sub>C</sub>	150	mW
	Power Dissipation Derating	ΔP <sub>C</sub> /°C	2.0 (*)	mW/°C
COUPLED	Storage Temperature Range	T <sub>stg</sub>	-55~150	°C
	Operating Temperature Range	T <sub>opr</sub>	-55~100	°C
	Lead Soldering Temperature (10s)	T <sub>sol</sub>	260	°C
	Total Package Power Dissipation	P <sub>T</sub>	250	mW
	Total Package Power Dissipation Derating	ΔP <sub>T</sub> /°C	3.3 (*)	mW/°C

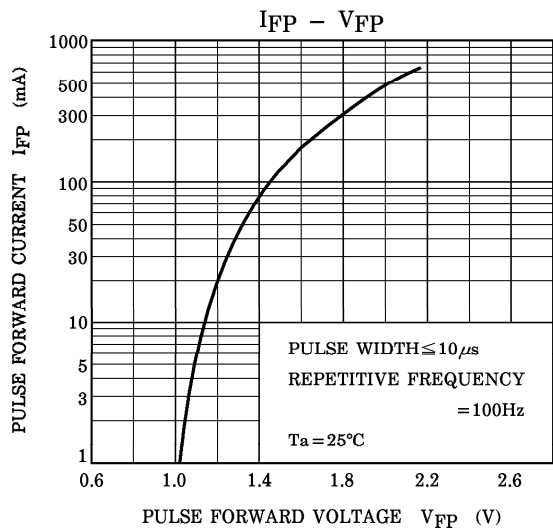
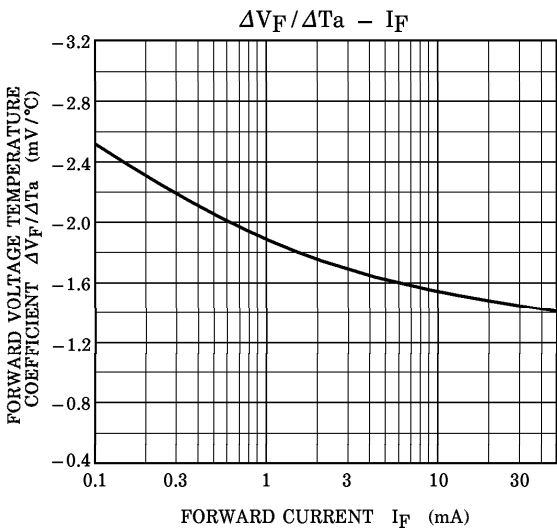
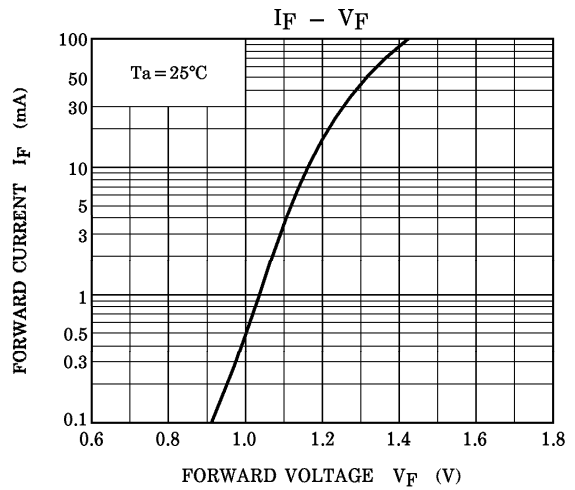
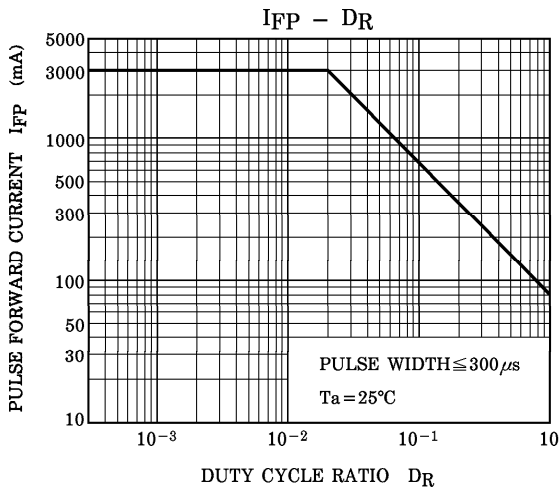
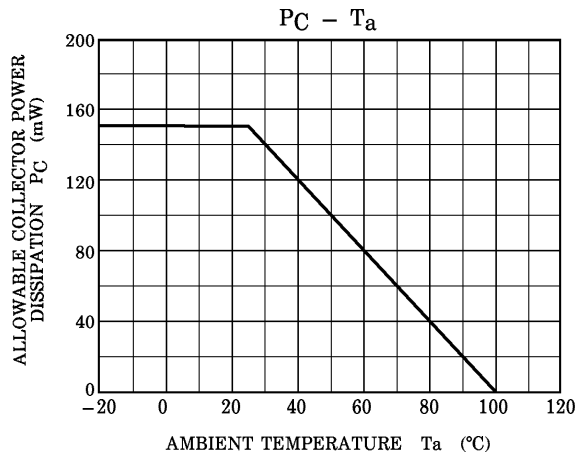
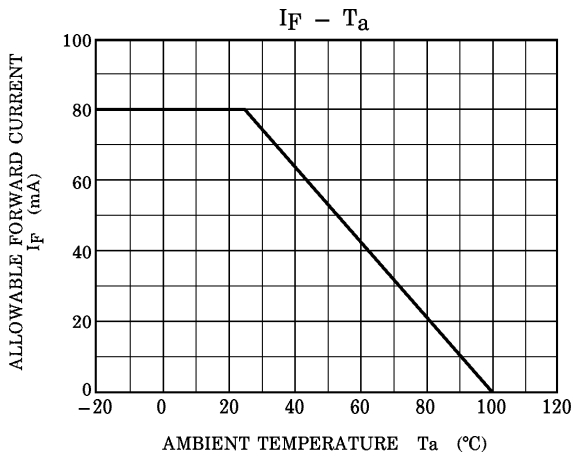
(Note 1) Pulse width 300μs, 2% duty cycle.

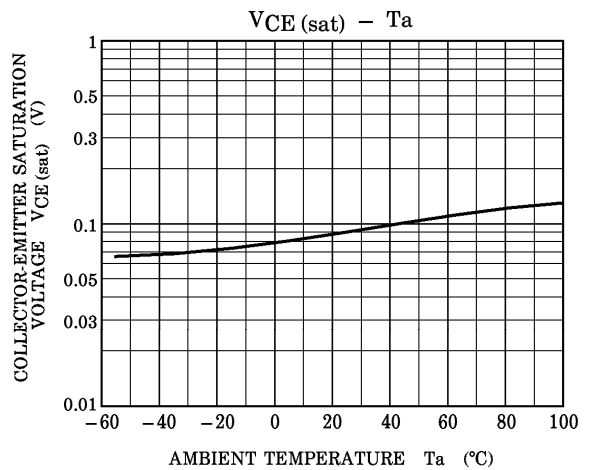
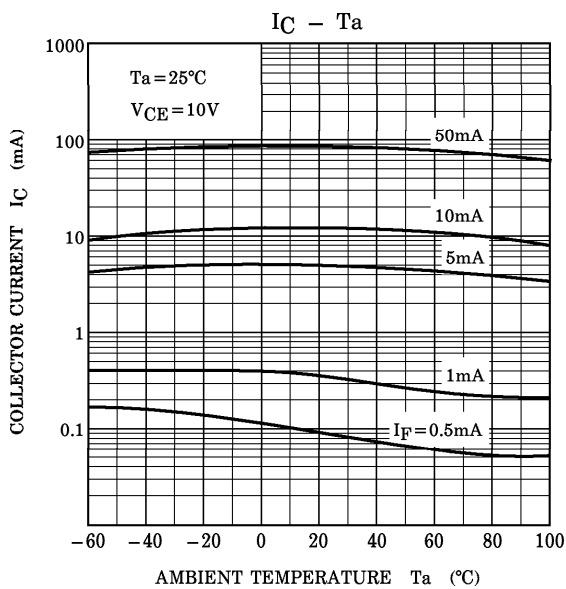
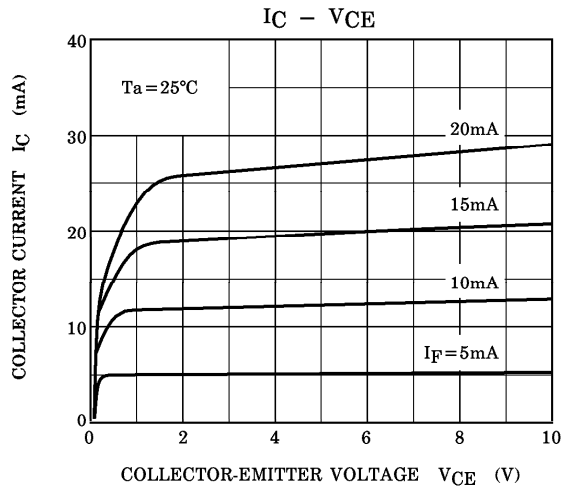
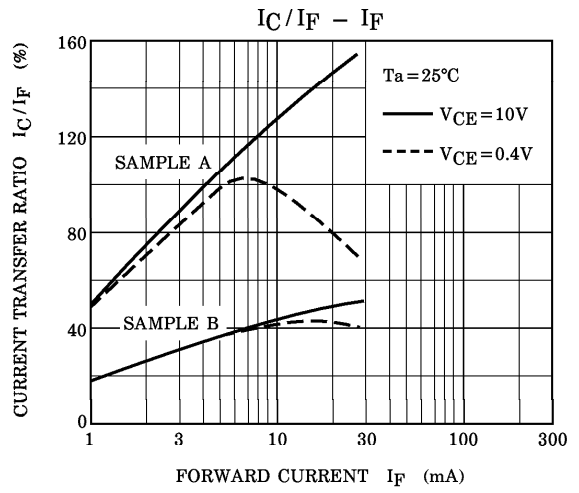
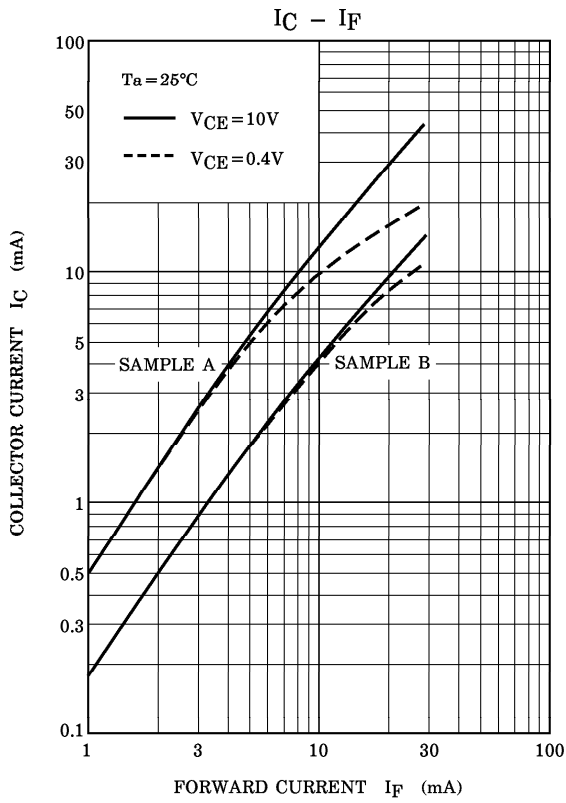
(\*) Above 25°C ambient.

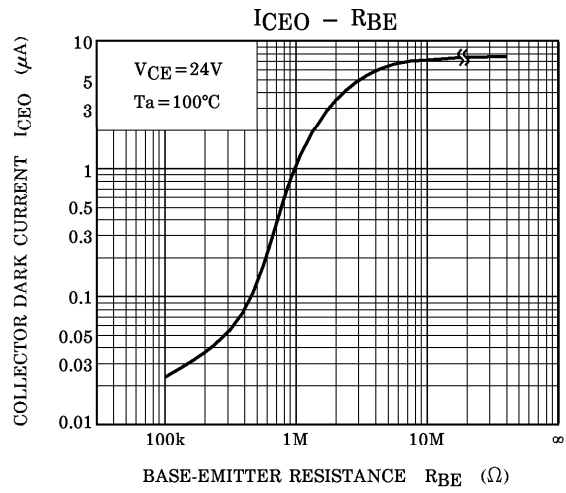
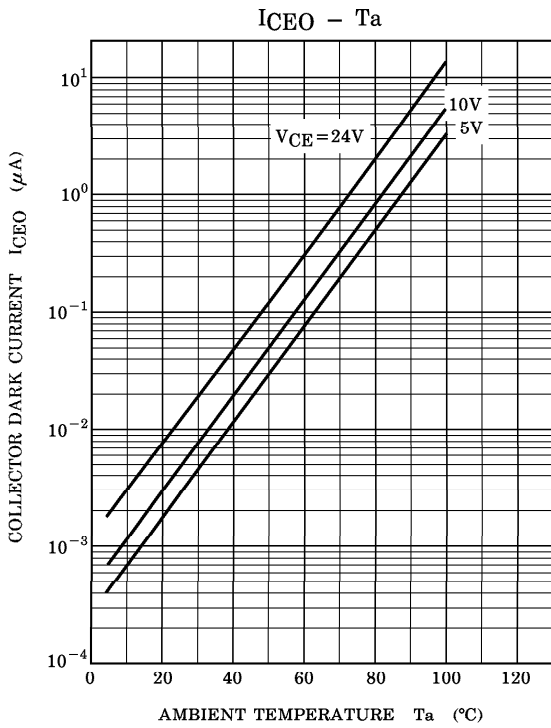
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
LED	Forward Voltage	$V_F$	$I_F = 10\text{mA}$	—	1.15	1.5	V	
	Reverse Current	$I_R$	$V_R = 3\text{V}$	—	—	100	$\mu\text{A}$	
	Capacitance	$C_D$	$V = 0, f = 1\text{MHz}$	—	30	—	pF	
DETECTOR	DC Forward Current Gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 500\mu\text{A}$	—	200	—	—	
	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_F = 0$	30	—	—	V	
	Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$	70	—	—	V	
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 100\mu\text{A}$	7	—	—	V	
	Collector Dark Current	$I_{CEO}$	$V_{CE} = 10\text{V}$	—	1	50	nA	
	Collector Dark Current	$I_{CBO}$	$V_{CB} = 10\text{V}$	—	0.1	20	nA	
	Collector-Emitter Capacitance	$C_{CE}$	$V = 0, f = 1\text{MHz}$	—	10	—	pF	
	Current Transfer Ratio	$I_C / I_F$	$I_F = 10\text{mA}, V_{CE} = 10\text{V}$	20	100	—	%	
COUPLED	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F = 50\text{mA}, I_C = 2\text{mA}$	—	0.1	0.5	V	
	Capacitance Input to Output	$C_S$	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF	
	Isolation Resistance	$R_S$	$V_S = 500\text{V}, R. H. \leq 60\%$	$10^{11}$	—	—	$\Omega$	
	Isolation Voltage		$BV_S$	AC, 1 minute	2500	—	—	$V_{rms}$
			$BV_S(*)$	AC, Peak	2500	—	—	$V_{pk}$
					1500	—	—	
					500	—	—	
			AC, 1 second	1775	—	—	$V_{rms}$	
	Rise / Fall Time	$t_r / t_f$	$V_{CE} = 10\text{V}, I_C = 2\text{mA}$ $R_L = 100\Omega$	—	2	—	$\mu\text{s}$	
	Rise / Fall Time	$t_r / t_f$	$V_{CB} = 10\text{V}, I_{CB} = 50\mu\text{A}$ $R_L = 100\Omega$	—	200	—	ns	

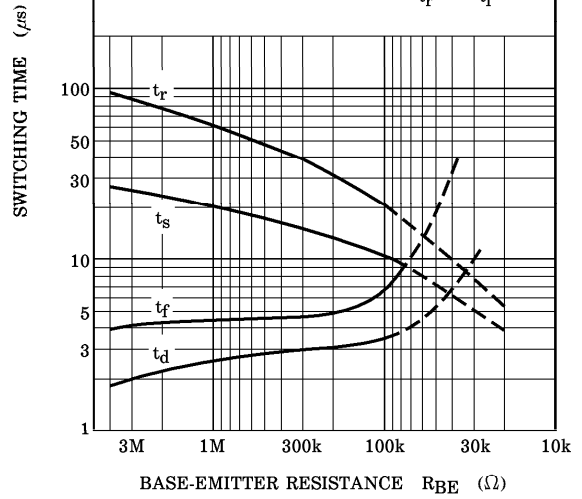
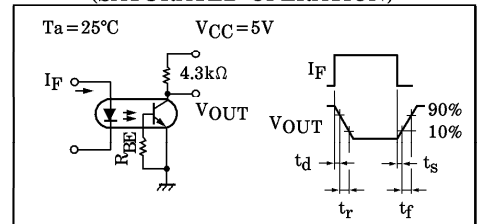
(\*) JEDEC registered minimum  $BV_S$ , however, TOSHIBA specifies a minimum  $BV_S$  of 2500Vrms, 1 minute.



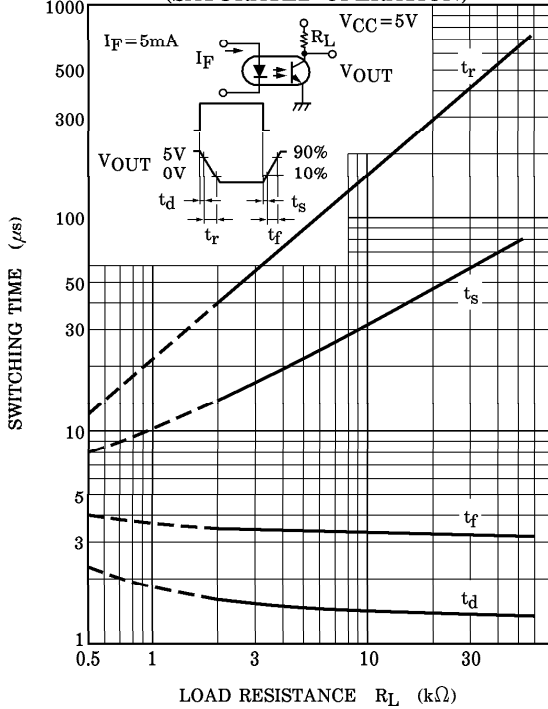




**SWITCHING CHARACTERISTICS -  $R_{BE}$   
(SATURATED OPERATION)**



**SWITCHING CHARACTERISTICS -  $R_L$   
(SATURATED OPERATION)**



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000707EBC

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